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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/712,062
				Filing Date	November 14, 2003
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2826
				Examiner Name	F. Abraham
Sheet	1	of	1	Attorney Docket Number	0756-7218

[illegible][illegible]

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

Examiner Signature	<i>Cheryl Morales</i>	Date Considered	<i>2/8/05</i>
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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				Examiner Name	Fetsum Abraham
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		Number	Kind Code <sup>2</sup> (if known)			
Pa		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
		5,922,125		Zhang	07/13/99	
		6,083,801		Ohtani	07/04/00	
		5,744,822		Takayama et al.	04/28/98	
		5,744,824		Kousai et al.	04/28/98	
		5,766,977		Yamazaki	06/16/98	
		5,773,846		Zhang et al.	06/30/98	
		5,773,847		Hayakawa	06/30/98	
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		5,795,795		Kousai et al.	08/18/98	
		5,808,321		Mitanaga et al.	09/15/98	
		3,890,632		Ham et al.	06/17/75	
		4,330,363		Biefesen et al.	05/18/82	
		4,466,073		Boyan et al.	08/14/84	
		5,543,636		Yamazaki	08/06/96	
		6,140,165		Zhang et al.	10/31/00	
		6,147,667		Yamazaki et al.	11/14/00	
		6,180,439 B1		Yamazaki et al.	01/30/01	
		5,929,527		Yamazaki et al.	07/27/99	
		5,949,107		Zhang	09/07/99	
		6,031,249		Yamazaki et al.	02/29/00	
		6,121,683		Yamazaki et al.	09/19/00	
		6,207,969 B1		Yamazaki et al.	03/27/01	

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		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

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		Number	Kind Code <sup>2</sup> (if known)			
PR		5,811,327		Funai et al.	09/22/98	
		5,818,076		Zhang et al.	10/06/98	
		5,821,138		Yamazaki et al.	10/13/98	
		5,824,574		Yamazaki et al.	10/20/98	
		6,175,348		Zhang et al.	01/16/01	
		5,728,259		Suzawa et al.	03/17/98	
		6,278,132 B1		Yamazaki et al.	08/21/01	
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		3,389,024		Schimmer	06/18/68	
		3,783,049		Sandera	01/01/74	
		4,059,461		Fan et al.	11/22/77	
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		4,174,217		Flatley	11/13/79	
		4,226,898		Ovshinsky et al.	10/07/80	
		4,231,809		Schmidt	11/04/80	
		4,271,422		Ipri	06/02/81	
		4,277,884		Hsu	07/14/81	
		4,300,989		Chang	11/17/81	
		4,309,224		Shibata	01/05/82	
		4,331,709		Risch et al.	05/25/82	
		4,379,020		Glaeser et al.	04/05/83	
		4,409,724		Tasch, Jr., et al.	10/18/83	
		4,472,458		Sirinyan et al.	09/18/84	
		4,481,121		Barthel	11/06/84	
		4,534,820		Mori et al.	08/13/85	
		4,544,418		Gibbons	10/01/85	

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Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)		
		JP	07-335900		12/22/95	Abst.
		JP	64-081324		03/27/89	Abst.

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PR		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

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		Number	Kind Code <sup>2</sup> (if known)			
B		4,546,376		Nakata et al.	10/08/85	
		4,597,160		Ipri	07/01/86	
		4,634,473		Swartz et al.	01/06/87	
		4,735,824		Yamabe et al.	04/05/88	
		4,755,481		Faraone	07/05/88	
		4,911,781		Fox et al.	03/27/90	
		4,959,247		Moser et al.	09/25/90	
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		4,996,077		Mosiehi et al.	02/26/91	
		4,996,523		Bell et al.	02/26/91	
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		5,075,259		Moran	12/24/91	
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		5,289,030		Yamazaki et al.	02/22/94	
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FAS		5,470,763		Hamada	11/28/95	
		5,480,811		Chiang et al.	01/02/96	
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		5,693,541		Yamazaki et al.	12/02/97	
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		5,717,224		Zhang	02/10/98	
		5,734,179		Chang et al.	03/31/98	
		5,773,327		Yamazaki et al.	06/30/98	
		5,786,796		Takayama et al.	07/28/98	
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		5,838,508		Sugawara	11/17/98	
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		5,899,547		Yamazaki et al.	05/04/99	
		5,929,464		Yamazaki et al.	07/27/99	
		5,933,205		Yamazaki et al.	08/03/99	
		5,940,732		Zhang	08/17/99	
		5,962,869		Yamazaki et al.	10/05/99	
		5,963,278		Yamazaki et al.	10/05/99	
		5,985,740		Yamazaki et al.	11/16/99	
		5,990,491		Zhang	11/23/99	
		5,990,542		Yamazaki	11/23/99	
		6,005,648		Zhang et al.	12/21/99	
		6,011,277		Yamazaki	01/04/00	

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FB		6,013,929		Ohtani	01/11/00	
		6,048,758		Yamazaki et al.	04/11/00	
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		6,077,731		Yamazaki et al.	06/20/00	
		6,093,934		Yamazaki et al.	07/25/00	
		6,100,562		Yamazaki et al.	08/08/00	
		RE 28,385		Mayer	04/08/75	
		RE 28,386		Heiman et al.	04/08/75	

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J		EP	0 178 447			10/09/84	English
		JP	01-187814			07/27/89	Full
		JP	01-187874			07/27/89	Abst.
		JP	01-187875			07/27/89	Abst.
		JP	01-206632			08/18/89	Abst.
		JP	02-140915			05/30/90	Full
		JP	02-148687			06/07/90	Abst.
		JP	02-275641			11/09/90	Abst.
		JP	03-280418			12/11/91	Abst.
		JP	03-280420			12/11/91	Full
		JP	05-082442			04/02/93	Abst.
		JP	05-107561			04/30/93	Abst.
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		JP	08-129358			05/21/96	Abst.
		JP	08-129359			05/21/96	Abst.
		JP	08-129360			05/21/96	Abst.
		JP	08-234683			09/13/96	Abst.
		JP	08-241047			09/17/96	Abst.
		JP	08-241048			09/17/96	Abst.
		JP	08-241057			09/17/96	Abst.
		JP	08-241997			09/17/96	Abst.
		JP	60-105216			06/10/85	Full
		JP	61-063017			04/01/86	Full
		JP	61-063107			04/01/86	Abst.
		JP	62-169356			07/25/87	Abst.

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PD		Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals," January 1, 1989, pp. 597-604, Applied Surface Science, Vol. 36	
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✓		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	7	of	12	Attorney Docket Number	0756-7218

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fa		Lau et al., "Solid Phase Epitaxy in Silicide Forming System," 1977, pp. 313-322, Thin Solid Films, 47	
		Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation," December 1990, pp. 2698-2704, Inst. Of Appl. Phys. Vol. 29, No. 12	
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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
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		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	

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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
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U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
P		5,705,829		Miyanaga et al.	01/06/98
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		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni-Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscopical Society Conf.	
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Po		5,403,772		Zhang et al.	04/04/95	
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		5,481,121		Zhang et al.	01/02/96	
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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
Sheet	11	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
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		Number	Kind Code <sup>2</sup> (if known)			
PK		5,932,893		Miyanaga et al.	08/03/99	
		4,759,610		Yanagisawa	07/26/88	
		5,535,471		Guldi	07/16/96	
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		5,210,050		Yamazaki et al.	05/11/93	
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PK		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

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FB		6,225,152	B1	Yamazaki et al.	05/01/01	
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		JP	06-314787			11/08/94		Ab

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		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	F. Abraham
Sheet 1	2	Attorney Docket Number	0756-7218

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F/A		6,162,704		Yamazaki et al.	12/19/2000	
		6,294,441		Yamazaki	09/25/2001	
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F/A		JP	07-066425		03/10/1995		Abst. & U.S. Equiv.
		JP	08-045839		02/16/1996		Abst. & U.S. Equiv.
		JP	08-045840		02/16/1996		Abst. & U.S. Equiv.
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		KR	96-005879		02/23/1996		U.S. Equiv.
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✓		JP	07-335906		12/22/1995		Abst. & U.S. Equiv.

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	10/712,062
		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	F. Abraham
Sheet 2 of 2	Patent & Trademark Office	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
P/A		2002/0025659		Yamazaki et al.	02/28/2002
		2002/0048891		Yamazaki et al.	04/25/2002
		6,423,586		Yamazaki et al.	07/23/2002

FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
✓		JP	07-192998			07/28/1995	Abst.
		JP	05-299339			11/12/1993	Abst. & U.S. Equiv.

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Examiner Signature	<i>F. Abraham</i>	Date Considered	2/8/05
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